

1 Ultra-bright, Efficient and Stable Perovskite Light- 2 Emitting Diodes

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24 **Abstract**

25 Metal halide perovskites are attracting great attention as next-generation light emitting
26 materials due to their excellent emission properties with narrowband emission.¹⁻⁴ However,
27 perovskite light-emitting diodes (PeLEDs) irrespective of their material types (**polycrystals** or
28 nanocrystals) have not realized high luminance, high efficiency and long lifetime
29 simultaneously, as they are influenced by the intrinsic limitations related to the trade-off
30 properties between charge transport and confinement in each type of perovskite materials.⁵⁻⁸
31 Here, we report an ultra-bright, efficient, and stable PeLEDs made of core/shell perovskite
32 nanocrystals with a size of ~10 nm obtained using simple *in-situ* reaction of benzylphosphonic
33 acid (BPA) additive with 3D polycrystalline perovskite films without separate synthesis
34 process. During the reaction, large 3D crystals are split into nanocrystals **and the BPA surrounds**
35 **the nanocrystals, achieving** strong carrier confinement. The BPA **shell** passivates the
36 undercoordinated lead atoms by forming covalent bonds, and thereby greatly reduces trap
37 density while maintaining good charge-transport properties of 3D perovskites. We demonstrate
38 simultaneously efficient, bright, and stable PeLEDs that have maximum brightness of ~470,000
39 cd m^{-2} , maximum external quantum efficiency of 28.9 % (average = 25.2 ± 1.6 % over 40
40 devices), maximum current efficiency of 151 cd A^{-1} , and half-lifetime of 520 h at $1,000 \text{ cd m}^{-2}$
41 (estimated half-lifetime >30,000 h at 100 cd m^{-2}). Our work sheds great light on the possibility
42 that PeLEDs can be commercialized in the future display industry.

43

44 Introduction

45 Metal halide perovskites (MHPs) are being studied as promising candidates for light
46 emitters due to their narrow emission spectra (full-width at half maximum (FWHM) ≈ 20 nm),
47 easy color tuning, excellent charge transport properties, and low-cost solution processability¹⁻
48 ⁴. Because of these advantages, research has mainly focused on achieving highly-efficient
49 operation of perovskite light-emitting diodes (PeLEDs). By introducing a perovskite
50 nanocrystal structure synthesized with organic ligands or cation alloying (e.g. FAGAPbBr₃),
51 high current efficiency of 108 cd A⁻¹ and external quantum efficiency (EQE) of 23.4 % were
52 achieved by realizing strong carrier confinement and bulk/surface defect suppression^{3,5-12}.
53 However, in these perovskite nanocrystal emitters, the insulating characteristics of organic
54 ligands can impede charge injection and transport, and thereby limit the brightness at the given
55 voltage and the operational lifetime despite their high luminous efficiency^{8,13-15}. In contrast,
56 3D polycrystalline perovskite (hereafter, 3D perovskite) film without such organic ligands has
57 good charge transport characteristics and simple fabrication processes (maximum luminance
58 $>100,000$ cd m⁻², device half-lifetime (T_{50}) > 200 h **at initial brightness = 100 cd m⁻²**), but
59 suffers from low luminous efficiency because of the poor charge confinement effect in the big
60 grains of >100 nm and non-radiative recombination defects at the grain boundary¹⁶⁻²⁰.
61 Although the improvements in both perovskite nanocrystals and 3D perovskites have enabled
62 drastic advances in the EQE of PeLEDs, due to the inevitable trade-off between these charge
63 confinement and charge transport, the state-of-the-art efficient PeLEDs with maximum EQE
64 >20 % mostly suffer from low brightness ($\sim 10,000$ cd m⁻²)^{7,10,15} and short T_{50} (< 100 h at initial
65 brightness = 100 cd m⁻²)¹⁰. Therefore, developing a perovskite material system that allow high
66 brightness, high efficiency and long device lifetime simultaneously is of great importance at
67 the current stage of research on PeLEDs.

68 Here, we developed a simple method to produce *in-situ* formed core/shell
69 nanoparticles (hereafter, *in-situ* core/shell) by reacting 3D perovskite films with
70 benzylphosphonic acid (BPA), which can split large crystals into perovskite nanoparticles
71 (PeNPs) and surround them to form PeNP@BPA composite, in which BPA exist as an organic
72 shell material²¹. Significantly reduced particle size of *in-situ* core/shell nanocrystals (10 ± 2
73 nm) compared with that of the 3D perovskites (205 ± 97 nm) showed significantly improved
74 carrier confinement, and the phosphonate group of BPA effectively passivated the defect sites

75 by binding covalently to undercoordinated Pb^{2+} . In the *in-situ* core/shell perovskite NPs, the
76 trap density was greatly decreased and the radiative recombination efficiency was significantly
77 increased compared to the 3D perovskites. PeLEDs based on *in-situ* core/shell structure showed
78 maximum current efficiency of 151 cd A^{-1} (maximum EQE of 28.9 %), maximum brightness
79 of $\sim 470,000 \text{ cd m}^{-2}$, very little efficiency roll-off ($\sim 5 \%$ even at $400,000 \text{ cd m}^{-2}$) and half-
80 lifetime of 520 h at initial brightness of $1,000 \text{ cd m}^{-2}$ (estimated half-lifetime $>30,000 \text{ h}$ at 100
81 cd m^{-2}) with green emission at EL peak of 540 nm, and therefore shows excellent efficiency,
82 luminance, and lifetime simultaneously.

83 **Results**

84 ***In-situ* nanostructure formation by BPA treatment**

85 We first show how post-treatment using BPA forms the *in-situ* nanostructure of the
86 perovskite crystal. 3D perovskite film of $(\text{FA}_{0.7}\text{MA}_{0.1}\text{GA}_{0.2})_{0.87}\text{Cs}_{0.13}\text{PbBr}_3$ was fabricated (left
87 of **Fig. 1a**) using the additive-based nanocrystal pinning (A-NCP) method³. In this case, ionic
88 defects with low formation energy exist on the crystal surface and inside the crystal, acting as
89 a cause of ion migration and carrier trapping, thereby significantly reducing the luminescence
90 efficiency and operational stability¹⁹. First, we added BPA as an additive into the precursor
91 solution, implementing an *in-situ* particle structure in which BPA cover the surface of crystals
92 by attaching as a ligand to the undercoordinated Pb on the surface of 3D perovskites (center of
93 **Fig. 1a**). The surface of the 3D perovskite film initially had an amorphous and irregular shape
94 due to a defective surface; after addition of up to 10 mol. % of BPA into the precursor, the
95 fabricated film developed a very clear cubic structure as the BPA molecules assembled on the
96 surface (**Extended Data Fig. 1**).

97 The perovskite thin film was further exposed to a BPA solution in tetrahydrofuran
98 (THF), forming *in-situ* core/shell perovskite NPs (right of **Fig. 1a**). Unlike other long alkyl
99 ligands (e.g. oleic acid, decylamine, and octylphosphonate), small BPA molecules with strong
100 acidity can penetrate and intercalate into large perovskite crystals²². After sufficient time is
101 provided for the BPA to intercalate into the crystal, BPA binds to the surface sites within the
102 crystal and splits the large crystal domain into a nanosized *in-situ* core/shell structure that is
103 surrounded by BPA.

104 The progressive particle refinement of large 3D perovskite grain to *in-situ* core/shell
105 perovskite NPs was observed by high-resolution transmission electron microscopy (TEM).
106 With increasing reaction time in BPA-THF solution, initially rectangular 3D crystals with size
107 of 200 nm showed gradual change in grain shape and decrease of grain size, and finally became
108 spherical *in-situ* core/shell structured nanograins with a size of 10 nm. (**Fig. 1b-i**) The *in-situ*
109 core/shell synthesis process was further confirmed using atomic-scale scanning transmission
110 electron microscopy (STEM) and scanning electron microscopy (SEM). At the beginning of
111 the reaction, BPA molecules bind to defective surfaces of large crystals that appear as dark
112 contrast regions or vague boundaries on STEM images, cracking the crystal out and thus
113 reducing the grain size (**Extended Data Fig. 2a-c**). The grain splitting reveals new defective
114 surfaces, and the cycle of BPA binding and breakage repeats and the grain size gradually
115 decreased with increased coverage of a BPA shell on the surface (**Extended Data Fig. 2d-g**).
116 Finally, when BPA molecules fully surround the 3D core that lacks a defective surface to which
117 BPA can bind, the *in-situ* core/shell structure is achieved (**Fig. 1e,i**). Perfect 3D lattice structure
118 in the core part and clear core/shell interface between perovskite and BPA molecule was
119 identified by STEM image and electron energy loss spectra (EELS) (**Fig. 1j-l, Extended Data**
120 **Fig. 3**). When the *in-situ* core/shell synthesis is finished, these *in-situ* core/shell grains are
121 located adjacent to each other, after being aggregated by the excess BPA molecules around
122 them to form macroparticles, as observed in SEM and TEM images and EDS maps (**Extended**
123 **Data Fig. 4-5**). The grain size distribution of these perovskite grains significantly decreased
124 from the 3D perovskite (205 ± 97 nm) to the *in-situ* particle structure (123 ± 34 nm) and further
125 to the *in-situ* core/shell structure (10 ± 2 nm) (**Supplementary Data Fig. 1**).

126

127 **Surface passivation of BPA shell**

128 To elucidate the mode of binding between BPA and the perovskite structure, we
129 performed X-ray photoelectron spectroscopy (XPS) and ultraviolet photoelectron spectroscopy
130 (UPS) analysis. The existence of BPA in perovskite films can be confirmed by emergence of
131 new peak at P 2p and O 1s spectra only in *in-situ* particle and *in-situ* core/shell perovskites
132 (**Supplementary Fig. 2a-b**). The O 1s spectrum of the BPA prior to any reaction shows the
133 main oxygen peak from the P-OH group at 533.0 eV and the P=O group at 531.5 eV in a ratio

134 of 2:1, which is consistent with previously-reported O 1s spectra of phosphonic acid derivatives
135 (**Fig. 2a**)^{23,24}. In contrast, in the O 1s peak of *in-situ* particles and *in-situ* core/shell perovskites,
136 a new peak around 531.0 eV appeared (**Fig. 2b-c**). This change can be ascribed to the formation
137 of covalent bonds during adsorption of phosphonate onto a metallic surface^{23,25}. i.e., BPA bonds
138 to the surface of perovskites by forming a new Pb-O-P covalent bond and replaces the bromide
139 vacancy site. In addition, the Pb 4f peak and the Br 3d peak of the BPA-induced structures are
140 shifted to higher binding energy than in the 3D perovskite structure. This difference can be
141 attributed to higher electronegativity of oxygen atoms compared with that of bromines, and
142 therefore modifying the Fermi level (**Supplementary Fig. 2c-d**). This can also be confirmed
143 by UPS analysis, which showed that the *in-situ* particle and *in-situ* core/shell particle have
144 much lower work function and higher energy offset between the work function and valence
145 band (**Supplementary Fig. 3, Fig. 2d**). This difference can arise from gradual diminishing of
146 self p-doping effects caused by ionic defects at the surface and within the crystal in 3D
147 perovskite and *in-situ* particle perovskite, which was suppressed in the *in-situ* core/shell
148 particle.

149

150 **Improvement in emission characteristics and defect passivation**

151 We analyzed the luminescence properties by conducting photoluminescence quantum
152 efficiency (PLQE) analysis. While perovskite thin films based on 3D and *in-situ* particle
153 structure showed comparably low internal quantum efficiency (IQE) of 30 % and 35 %
154 respectively, *in-situ* core/shell perovskite film showed greatly high IQE of 88 % (**Extended**
155 **Data Fig. 6a-c**). Steady-state PL spectra and time-correlated single photon counting (TCSPC)
156 measurement also confirmed higher PL intensity and longer PL lifetime in *in-situ* core/shell
157 structure compared to that in 3D and *in-situ* particle perovskites (**Fig. 3a-b**). The great
158 improvement of IQE can be realized by reducing the particle size to strengthen charge
159 confinement and defect density by passivating defects, i.e., undercoordinated Pb atoms and
160 halide vacancies, which act as non-radiative recombination centers in the perovskite emitter.
161 The improved charge confinement was confirmed by temperature-dependent PL analysis (**Fig.**
162 **3c-e, Extended Data Fig. 6d-i**). From 3D to *in-situ* particle and *in-situ* core/shell structure, the
163 peak center was blue-shifted, and the exciton binding energy (E_b) was increased from 90 meV

164 to 220 meV; this change indicates that the *in-situ* core/shell structure experiences a strong
165 confinement effect from the grain size reduction.

166 To further confirm the passivation effect of BPA-induced nanostructure, we performed
167 trap-density analysis by fabricating hole-only device (HOD) and analyzing the transport
168 characteristics (**Supplementary Fig. 4**). The current-voltage (I-V) characteristics of these
169 HOD can be classified into three types of region according to the slope (k), Ohmic region ($k =$
170 1) in the low-injection regime, a trap-filled limited (TFL) region ($k > 3$), and a space-charge
171 limited current (SCLC) regime ($k = 2$)²⁶. In this, the total trap state density inside the perovskite
172 film can be calculated as

$$173 \quad n_t = 2\epsilon\epsilon_0 V_{TFL} / (eL^2)$$

174 where n_t is the trap state density, V_{TFL} is the trap-filled limit voltage, L is the thickness of the
175 perovskites, e is the elementary charge, ϵ_0 and ϵ are the vacuum permittivity and relative
176 permittivity, respectively. By estimating V_{TFL} as the intersection between ohmic region and
177 TFL region, we calculate $n_t = 3.50 \times 10^{16} \text{ cm}^{-3}$ for 3D, $n_t = 2.36 \times 10^{16} \text{ cm}^{-3}$ for *in-situ* particle, n_t
178 $= 1.37 \times 10^{16} \text{ cm}^{-3}$ for *in-situ* core/shell perovskites. This result is evidence that the passivation
179 effect of BPA-induced nanostructure in perovskite films also contributes to the increased
180 luminescent efficiency. We also calculated the hole mobility (μ_h) of each device by applying
181 the Mott–Gurney law equation in the Child region of trap-free SCLC transport as below.

$$182 \quad \mu_h = \frac{8L^3 J}{9\epsilon\epsilon_0 V^2}$$

183 Here, J is the current density, and V is the voltage. All devices had similar μ_h : $3.26 \times 10^{-2} \text{ cm}^2$
184 $\text{V}^{-1} \text{ s}^{-1}$ with 3D, $3.08 \times 10^{-2} \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ with *in-situ* particle, and $2.99 \times 10^{-2} \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ with *in-*
185 *situ* core/shell perovskites. This result indicates that fast charge transport property in 3D
186 perovskites could be preserved in the *in-situ* core/shell structure because excessive insulating
187 ligand was not used.

188 **Light-emitting diode performance**

189 Encouraged by simultaneously increased PL efficiency, decreased trap density, and
190 preserved fast charge transport, we fabricated LEDs based on the BPA-induced nanostructured
191 perovskites (**Fig. 4a**, **Supplementary Fig. 5**). The PeLEDs based on *in-situ* core/shell

192 perovskites showed maximum current efficiency of 151 cd A^{-1} and maximum EQE of 28.9 %,
193 calculated using the full angular electroluminescence distribution (**Fig. 4b-c, Extended Data**
194 **Fig. 7a-g**)²⁷. In contrast to many previously-reported OLEDs and PeLEDs that have ultrathin
195 EMLs ($< 50 \text{ nm}$), this is a remarkably high EQE with an EML $> 200 \text{ nm}$ in devices in which
196 the microcavity effects are diluted. The result emphasizes the important role of photon
197 recycling effect in thick EMLs²⁸⁻³¹. Optical simulation verified that our PeLEDs can reach EQE
198 of 29.2 % with an aid of photon recycling effect (**Supplementary Fig. 6**). The detailed current-
199 voltage-luminance characteristics are summarized in **Extended Data Table 1**. Also, the
200 distribution of EQE and luminance obtained from 40 devices showed great reproducibility (**Fig.**
201 **4d, Extended Data Fig. 7h**). Especially, to manufacture efficient *in-situ* core/shell PeLEDs
202 with great reproducibility, the crystallization process of as-synthesized perovskite thin films
203 must be controlled so that the grain size does not increase too much before the *in-situ* reaction
204 with BPA. When the A-NCP timing is not delayed and the processing temperature is kept $<$
205 $18 \text{ }^\circ\text{C}$, the grain size can be sufficiently small ($< 100 \text{ nm}$), so that BPA can completely penetrate
206 them during the reaction, and thereby provide nanostructures that are favorable for obtaining
207 high-efficiency devices (**Extended Data Fig. 7i**). The PeLEDs showed high maximum
208 brightness of $473,990 \text{ cd m}^{-2}$ whereas 3D PeLEDs and *in-situ* particle PeLEDs showed
209 maximum brightness of only $20,271 \text{ cd m}^{-2}$ and $149,331 \text{ cd m}^{-2}$, respectively. The maximum
210 brightness of *in-situ* core/shell PeLEDs is the highest so far reported among PeLEDs based on
211 any of the 3D, quasi-2D, or perovskite nanocrystals, and is even comparable with the highest
212 brightness of state-of-the-art inorganic quantum dot (QD) LEDs (**Fig. 4e**)³². Furthermore, due
213 to the fast charge transport with high IQE, we could realize ultralow driving voltage of 2.7 V
214 at brightness of $10,000 \text{ cd m}^{-2}$, which is much lower than the driving voltage of any other state-
215 of-the-art LEDs based on Quasi-2D (4.7 V), PeNC ($\sim 6 \text{ V}$), or organic $\text{Ir}(\text{ppy})_2(\text{acac})$ ($\sim 4.8 \text{ V}$)
216 (**Supplementary Table 1**). *In-situ* core/shell PeLEDs also maintained the EQE value of $\geq 20 \%$
217 under ultra-high brightness conditions from $50,000 \text{ cd m}^{-2}$ to $400,000 \text{ cd m}^{-2}$, and exhibited
218 very low roll-off of $\sim 5 \%$ at luminance of $400,000 \text{ cd m}^{-2}$ (**Supplementary Table 2**). These
219 results are remarkable considering that reported high-efficiency nanocrystal PeLEDs with EQE
220 $> 20 \%$ have low brightness ($\sim 10,000 \text{ cd m}^{-2}$) and large efficiency roll-off ($> 50 \%$ at $> 10,000$
221 cd m^{-2}), because they use insulating ligands and therefore have thickness of emitting layer
222 mostly $< 30 \text{ nm}$ to compensate its poor charge-transporting characteristics and to strengthen

223 light outcoupling from the device (**Fig. 4e**). In contrast, *in-situ* core/shell perovskites are
224 formed by *in-situ* treatment of 3D perovskites without long insulating ligands, so both high
225 efficiency and high brightness could be realized without significantly sacrificing charge
226 transport, **which in turn resulted in low-efficiency roll-off because of better charge balance with**
227 **higher charge transport and thus no severe charge accumulation**. We also fabricated bright
228 large-area PeLEDs (pixel size: 120 μm^2) based on *in-situ* core/shell structure. These PeLEDs
229 had high uniformity and efficiency >20 %; these results show the potential of hybrid perovskite
230 emitters for use in solid-state lighting and display applications (**Fig. 4f, Extended Data Fig.**
231 **8**).

232 Finally, the operational lifetime of the PeLEDs were analyzed by applying a constant
233 current and monitoring the luminance. Compared with the T_{50} of 3D (0.2 h) and *in-situ* particle
234 (3.5 h) PeLEDs at initial brightness (L_0) = 10,000 cd m^{-2} , *in-situ* core/shell PeLEDs showed
235 much longer T_{50} of 14 h, due to greatly improved luminescent efficiency without sacrifice of
236 charge-transport properties (**Extended Data Fig. 9**). The operational lifetime of *in-situ*
237 core/shell PeLEDs was further measured at various L_0 from 1,000 cd m^{-2} to 200,000 cd m^{-2}
238 (**Fig. 4g-h**). Specifically, *in-situ* core/shell PeLEDs showed ultra-long T_{50} of 520 h at 1,000 cd
239 m^{-2} . By using the accelerated lifetime equation ($L_0^n T_{50} = \text{constant}$, where n is an acceleration
240 factor)^{33,34} with $n = 1.68$ over 21 devices, we estimated the device's T_{50} at 100 cd m^{-2} to be
241 31,808 h, which is, to our knowledge, the highest T_{50} estimated to date in PeLEDs (**Fig. 4h-i,**
242 **Supplementary Table 3**).

243 **Conclusions**

244 We demonstrated *in-situ* core/shell perovskite nanocrystals with size of ~ 10 nm by
245 using *in-situ* reaction of BPA molecule with 3D perovskite thin films. In the process of reaction,
246 BPA molecules penetrated into large 3D perovskite crystals and split them into nanosized
247 crystals, thus surrounding it as a core/shell structure. This *in-situ* core/shell NP structure
248 enabled increased carrier confinement, reduction in trap density, and increase in luminous
249 efficiency without sacrificing the charge transport properties of 3D perovskites. As a result,
250 simultaneously ultra-bright, efficient and stable PeLEDs with maximum current efficiency of
251 151 cd A^{-1} (maximum EQE of 28.9 %), maximum luminance of $\sim 470,000$ cd m^{-2} , very low
252 efficiency roll-off of ~ 5 % at 400,000 cd m^{-2} , and half-lifetime of 520 h at initial brightness of

253 1,000 cd m⁻² (estimated half-lifetime >30,000 h at 100 cd m⁻²) were demonstrated. These results
254 suggest that PeLEDs are not only laboratory-level high-efficiency devices but are promising
255 candidates for commercial self-emissive displays and lighting applications that require ultra-
256 high brightness and long operational lifetime comparable to those of state-of-the-art OLEDs or
257 QD LEDs.

258

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337

338 **Acknowledgements** This work was supported by the National Research Foundation of Korea
339 (NRF) grant funded by the Korea government (Ministry of Science, ICT & Future Planning)
340 (NRF-2016R1A3B1908431). G.-S.P was supported by the DGIST R&D Program (22-CoE-
341 NT-02) by the Korea government (Ministry of Education and Ministry of Science, ICT &
342 Future Planning).

343

344 **Author Contributions** J.S.K., J.-M.H. equally contributed to this work. J.S.K., J.-M. H. and
345 T.-W.L. initiated and designed the study. J.S.K and J.-M.H. fabricated LED devices and
346 analyzed data. G.-S.P. performed the TEM measurement. H.J.Y. conducted the UPS and XPS
347 analysis. S.-J. W. and D.-H. Kim conducted the temperature-dependent PL and
348 photoluminescence quantum efficiency analysis. S.-J.W. and C.C conducted the optical
349 simulation of the devices. J.P. assisted to analyze the TCSPC data. S.-C.L. provided support
350 for the characterization of the materials. S.-H.P. and E.Y. assisted the fabrication of LED
351 devices. T.-W.L. supervised the work. J.S.K. drafted the first version of the manuscript, with
352 assistance from J.-M.H. and T.-W.L. All authors discussed the results and commented on the
353 manuscript.

354 **Competing interests** The authors declare no competing interests.

355

356

357 **Fig. 1 | Emergence of *in-situ* core/shell perovskite with BPA treatment.** **a**, Schematic
358 illustration of the transformation process of 3D (left) into *in-situ* particle (middle) and *in-situ*
359 core/shell (right) structure by BPA treatment. TEM image of perovskite nanograins during *in-*
360 *situ* core/shell synthesis process with reaction time of **b**, 1 s, **c**, 10 s, **d**, 20 s, **e**, 30 s. (insets:
361 low-magnification TEM images). **f-h**, High-resolution TEM images of the boxed regions in **b-**
362 **d**. (insets: FFT-diffractograms showing the cubic lattice structure) **i**, High-resolution HAADF-
363 STEM image of the single *in-situ* core/shell NP taken from the boxed region in **e**, showing a
364 flat interface between the perovskite core and the BPA shell. **j**, Atomically resolved HAADF-
365 STEM image of the core region taken from the *in-situ* core/shell perovskite NP with atomic
366 structure model, showing the perfect 3D perovskite crystal structure. **k**, High-resolution STEM
367 image focusing on surface region of *in-situ* core/shell. **l**, the EEL spectra acquired from the
368 positions A and B highlighted in **k**. The Si peak is a background signal from the silicon nitride
369 TEM window grid.

370 **Fig. 2 | Surface passivation of BPA ligand.** **a-c**, O 1s XPS core-level spectra of **a**, BPA, **b**, *in-*
371 *situ* particle perovskite, **c**, *in-situ* core/shell perovskite. **d**, Energy level diagram of the pristine
372 3D, *in-situ* particle, *in-situ* core/shell perovskites obtained from parameters derived from UPS
373 spectra.

374 **Fig. 3 | Luminescent property and defect passivation with BPA treatment.** **a**, Steady-state
375 PL spectra and **b**, PL lifetime curves of Glass/BufHIL/Perovskite thin films that used 3D, *in-*
376 *situ* particle, and *in-situ* core/shell structure. For comparison, PL intensity of 3D and *in-situ*
377 particle perovskites in **a** were 10 times magnified. **c-e**, Two-dimensional (2D) map of
378 temperature-dependent PL spectra of 3D, *in-situ* particle, *in-situ* core/shell perovskite film
379 respectively (normalized to peak value).

380 **Fig. 4 | EL characteristics of PeLEDs with BPA treatment.** **a**, schematics of energy
381 diagram of PeLEDs. **b**, luminance vs voltage, **c**, EQE vs luminance, and **d**, EQE histogram of
382 PeLEDs. **e**, Summary of the reported green PeLEDs characteristics based on maximum EQE
383 and luminance. **f**, Photograph of operating large-area device. (pixel size: 120 mm²) **g**,
384 Luminance vs time of PeLEDs based on *in-situ* core/shell perovskites at various initial
385 brightness. **h**, half-lifetime vs brightness from accelerated lifetime test of *in-situ* core/shell
386 structure PeLEDs. **i**, Summary of the reported PeLEDs characteristics based on maximum
387 EQE and estimated or measured half-lifetime at 100 cd m⁻².

388

389 **Methods**

390 **Materials.** Formamidinium bromide (FABr, > 99.99 %), methylammonium bromide (MABr,
391 > 99.99 %), and guanidinium bromide (GABr, > 99.99 %) were purchased from Dyesol.
392 Cesium bromide (CsBr), BPA, tetrafluoroethylene-perfluoro3,6-dioxa-4-methyl-7-octene-
393 sulfonic acid copolymer (PFI), chlorobenzene (CB), tetrahydrofuran (THF), and molybdenum
394 oxide (MoO₃) were purchased from Sigma-Aldrich. Lead bromide (PbBr₂ >98.0 % (T)) was
395 purchased from TCI Co., Ltd. 2,2',2''-(1,3,5-benzinetriyl)-tris(1-phenyl-1-H-benzimidazole)
396 (TPBi) was purchased from OSM. 9,10-di(naphthalene-2-yl)anthracen-2-yl-(4,1-
397 phenylene)(1-phenyl-1H-benzo[d]imidazole) (ZADN) was purchased from Shinwon
398 Chemtrade Co., Ltd. Lithium fluoride (LiF) was supplied from Foosung Co., Ltd. Unless
399 otherwise stated, all materials are used without purification.

400

401 **Preparation of MHP solution.** The mixed-cation precursor,
402 ((FA_{0.7}MA_{0.1}GA_{0.2})_{0.87}Cs_{0.13}PbBr₃) was prepared by dissolving stoichiometric ratio of each of
403 FABr, MABr, GABr, CsBr and PbBr₂ (molar ratio (FABr + MABr + GABr + CsBr) : PbBr₂ =
404 1.15 : 1) in DMSO at a concentration of 1.2 M^{7,35}. In case of precursor solution for the *in-situ*
405 particle perovskite, 10 mol. % of BPA relative to PbBr₂ were added. The solution was stirred
406 overnight in N₂-filled glove box at room temperature before use.

407

408 **Fabrication of PeLEDs.** Pre-patterned FTO(350 nm, 12-14 Ω/sq, 25 mm × 25 mm, Nippon
409 Sheet Glass Co., Ltd.) glasses were sonicated in acetone and 2-propanol for 15 min each
410 sequentially, then boiled in 2-propanol for 30 min. The surface of FTO substrates undergoes
411 ultraviolet-ozone (UVO) treatment to achieve hydrophilic surface. We used a previously-
412 described method to **prepare** a HIL (BufHIL) that has a gradient work function (WF), by
413 inducing **vertical** self-organization of PEDOT:PSS (CLEVIOS P VP AI4083) and
414 tetrafluoroethylene-perfluoro3,6-dioxa-4-methyl-7-octene-sulfonic acid copolymer (PFI) **to**
415 **have surface-enriched PFI buffer layer**; the solution with 1:1 weight ratio of PEDOT:PSS to
416 PFI was spin-coated to form 75-nm thickness, then annealed at 150 °C for 30 min¹. After
417 baking, the substrates were transferred into a N₂-filled glove box for deposition of MHP
418 layer. MHP films with thickness of 270 nm were deposited by spin-coating the precursor
419 solution at 6000 rpm with additive-assisted nanocrystal pinning (NCP) process:³ during the

420 second spin step, TPBi-dissolved CB solution was dropped onto the spinning perovskite film.
421 For synthesis of *in-situ* core/shell perovskite film, BPA dissolved in THF solution was loaded
422 on top of the perovskite, followed by reaction time of 30s and direct spin-drying afterward.
423 Samples were then moved to the vacuum chamber ($<10^{-7}$ Torr) to sequentially deposit ZADN
424 (45 nm), LiF (1.2 nm), and Al (100 nm). The active area of 4.9 mm^2 was defined by shadow
425 masking during deposition of cathode. Finally, the fabricated PeLEDs were encapsulated in a
426 glovebox under a controlled N_2 atmosphere ($\text{O}_2 < 10.0 \text{ ppm}$, $\text{H}_2\text{O} < 1.0 \text{ ppm}$) by using a glass
427 lid and UV-curable epoxy resin with 15 min of UV (365 nm) treatment.

428

429 **Perovskite film characterizations.** Images of the surfaces were obtained using a field-
430 emission scanning electron microscope (SEM) (SUPRA 55VP). XPS and UPS spectra were
431 measured by using a photoelectron spectrometer (AXIS-Ultra DLD, Kratos Inc.). A
432 monochromatic Al-K α line (1486.6 eV) was used for XPS, and He I radiation (21.2 eV) was
433 used for UPS. Steady-state photoluminescence (PL) spectra and ultraviolet/visible (UV-Vis)
434 absorption spectra were measured by using a JASCO FP8500 spectrofluorometer and
435 Lambda-465 UV-Vis spectrophotometer. For transient PL decay measurement, a system
436 composed of a streak camera (c10627, Hamamatsu Corp.) and a nitrogen pulse laser (337 nm,
437 20 Hz, Usho Inc.) was used. PLQY was measured with a PMT and monochromator (Acton
438 Research Corporation) using a 325 nm He:Cd CW laser (Kimmon Koha) at the excitation
439 power of 62.5 mW cm^{-2} . Direct and indirect emission from the perovskite film was measured
440 to determine the accurate PLQY values. For the temperature-dependent PL measurement, the
441 sample was mounted in a cryostat (Advanced Research Systems, Inc.) under vacuum and the
442 emission spectrum was analyzed using a 405 nm laser diode (PicoQuant) at excitation power
443 of $34 \mu\text{W cm}^{-2}$. For single-carrier device analysis, MoO_3 (30 nm) and Au (50 nm) were
444 thermally deposited sequentially onto FTO / BufHIL / perovskite and encapsulated in N_2
445 atmosphere to obtain the current-voltage curve using a Keithley 236 source measurement
446 unit.

447

448 **Transmission electron microscopy characterizations.**

449 Perovskite thin films were deposited on a 5-nm-thick silicon nitride membrane using the same
450 spin-coating conditions as for the actual device. The membrane, with a size of

451 100 $\mu\text{m} \times 1,500 \mu\text{m}$, is supported on a 100- μm -thick silicon frame. The silicon nitride
452 membrane grid was loaded on a sample holder for TEM characterization without further
453 processing of TEM sample preparation. Double Cs-corrected (S)TEM systems (Themis Z,
454 Thermo Fischer Scientific) equipped with EELS (Quantum ER965, Gatan) and EDX (Super-
455 X EDS system) were used for atomic-scale structure imaging and chemical analysis of the
456 samples at an accelerating voltage of 200 kV. Due to the electron beam damage of core/shell
457 perovskite nanocrystals by high-energy electron illumination in TEM, we acquired high-
458 resolution TEM images, high-resolution STEM-HAADF images, and EELS and EDS data at
459 the low dose-rates. Core-loss EELS using a 2 Å nominal probe size and 1.8-2.0 eV energy
460 resolution were obtained with exposures of 12 sec (integrated by 60 scans with each taking for
461 0.2 sec). EELS entrance aperture of 5 mm, and an energy dispersion of 0.5 eV/ch and 1.0 eV/ch
462 were used for high-loss EELS (>1500 eV).

463

464 **Characterization on efficiency of PeLEDs.**

465 Electroluminescence efficiencies of the fabricated PeLEDs were measured using a Keithley
466 236 source measurement unit and a Minolta CS-2000 spectroradiometer. External quantum
467 efficiency of PeLEDs was calculated by measuring full angular electroluminescence
468 distribution²⁷. **The accuracy of the analysis was cross-checked by conducting an independent**
469 **analysis at the University of Cambridge with same devices, from which we confirmed**
470 **consistent results (Supplementary Fig. 7).**

471

472 **Lifetime analysis of PeLEDs.** Operational lifetime of PeLEDs was measured under constant
473 current condition by simultaneously tracking brightness and applied voltage using a M760
474 Lifetime Analyzer (McScience Inc.) with a control computer **under air-conditioned**
475 **environment below 18°C.**

476

477 **Optical Simulation.** Outcoupling efficiency, perovskite reabsorption A_{act} , and parasitic
478 absorption A_{para} were obtained from the calculated Poynting vectors at each interface of glass
479 ($n = 1.5$, incoherent)/ FTO ($n = 1.9$, 350 nm)/ BufHIL ($n = 1.5$, 75 nm)/ perovskite / ZADN
480 ($n = 2$, 45 nm)/ LiF ($n = 1.4$, 1.2 nm)/ Al (n from literature³⁶), by using a recently-proposed
481 method^{30,31} (n : refractive index). The imaginary part of the refractive index spectrum of

482 perovskite was obtained from the measured absorbance, while the real part was assumed to
483 be constant ($n_{\text{perov}} = 2.3$). The internal radiation spectrum was obtained by the reverse
484 calculation from the measured external radiation spectrum. The maximum EQE values with
485 photon recycling effect were obtained at each perovskite thickness, by integrating the results
486 for dipoles with various wavelengths, orientations (vertical and horizontal), polarizations (s
487 and p), and positions (20 positions uniformly distributed over the perovskite layer). The
488 relationship between external and internal PLQE was calculated in the same way, for the
489 structure of glass/ perovskite.

490

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495

496 **Data availability**

497 The data that support the findings of this study are available from the corresponding authors
498 upon reasonable request.

499

500 **Extended Data Fig. 1 | Morphology of *in-situ* particle perovskite thin films.** SEM images
501 of perovskite thin films made of 1.2M precursor solution with **a**, 0 % (3D), **b**, 2.5 %, **c**, 5 %,
502 **d**, 10 % (*in-situ* particle) molar ratio of BPA molecule relative to PbBr₂. **e**, HAADF-STEM
503 image and EDS elemental maps of P (green), Br (yellow), and Pb (red), respectively. **f**,
504 HAADF-STEM image and EDS elemental maps of a single perovskite grain showing the
505 uniform dispersion of P (green), Br (yellow), and Pb (red) on the grain.

506 **Extended Data Fig. 2 | Morphological characterization during *in-situ* core/shell**
507 **nanoparticle synthesis process.** **a**, SEM image of a perovskite thin film (after 1s of reaction
508 time with BPA-THF solution) showing small grains cracked out from large 3D grain. **b**, STEM
509 image of 50 nm-size perovskite crystal during *in-situ* core/shell synthesis process. Yellow
510 arrows indicate the defective perovskite surfaces that can be bound with BPA. **c**, HR-TEM
511 image of another perovskite crystal showing ultra-small nanocrystals segregated during *in-situ*
512 core/shell synthesis process. Insets: Magnified HR-TEM images of ultra-small nanocrystals
513 taken from the white-boxed regions labelled C1 and C2. **d-e**, High-resolution HAADF-STEM
514 images of single perovskite nanograins with decreasing grain size. Magnified HAADF-STEM
515 images of the grain surfaces (D1, D2, E1, E2, F1, F2, G1, G2) demonstrate that the BPA shell
516 coverages on the grain surfaces gradually increase and the defective surface regions decrease
517 as the grain size decreases.

518 **Extended Data Fig. 3 | Characterization of perovskite/BPA core/shell interface.** **a**, High-
519 resolution HAADF-STEM image of single perovskite grain formed during *in-situ* core/shell
520 synthesis process. **b, c**, Atomic-scale HAADF-STEM (**b**) and ABF-STEM (**c**) images of the
521 boxed area denoted in **a**. **d,e**, Magnified HAADF-STEM (**d**) and ABF-STEM (**e**) images of the
522 boxed area shown in **b** and **c** to indicate the positions of EELS acquisition. **f**, EEL spectra
523 acquired at the atomic positions labelled A, B, and C in **d, e**. **g**, EEL spectrum in the energy-
524 loss range of the N-K and O-K edges acquired at the position labelled C. The O-K peak
525 indicates the presence of BPA shells, but N-K peak is simply a background signal from the
526 silicon nitride TEM window grid.

527 **Extended Data Fig. 4 | SEM image of low-concentration (0.6 M) perovskite thin films**
528 **with different reaction time between BPA solution and perovskite thin film.** **a**, 3D
529 perovskites without reaction, **b**, 1 s, **c**, 15 s, **d**, 30 s of exposure time to BPA-THF solution
530 before spin-drying. Colored regions indicate *in-situ* particle perovskites (red) and *in-situ*
531 core/shell perovskites (green). **e**, Schematic illustration of the growth process of BPA
532 macroparticle domain and perovskite crystal forming *in-situ* core/shell structure.

533 **Extended Data Fig. 5 | HAADF-STEM analysis of *in-situ* core/shell perovskites.** **a**, TEM
534 image and **b, c**, magnified HAADF-STEM images of *in-situ* core/shell thin films. **d**, HAADF-
535 STEM image of *in-situ* core/shell grains and EDS elemental maps of P (red), Pb (yellow), and
536 Br (green), respectively. The EDS maps clearly show the uniform dispersion of P (red) over
537 macrograins. **e**, HAADF-STEM image of single macrograins consists of *in-situ* core/shell
538 nanoparticles. **f**, EDS spectrum acquired at the location of the red circled region in **e**.

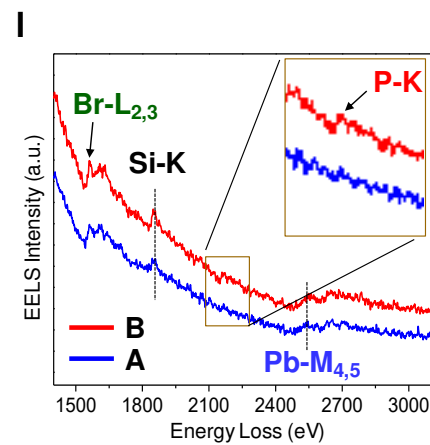
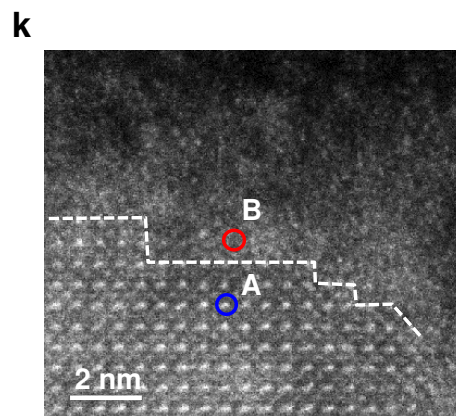
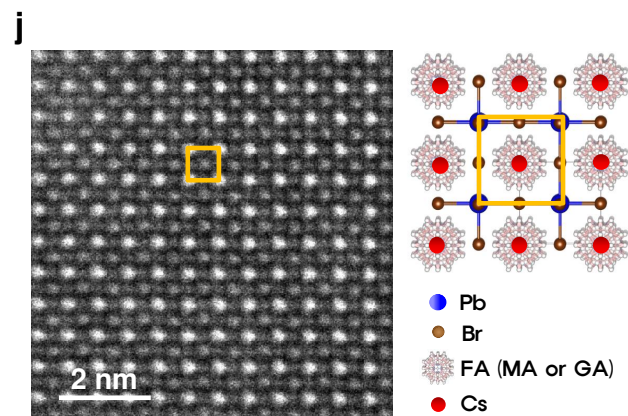
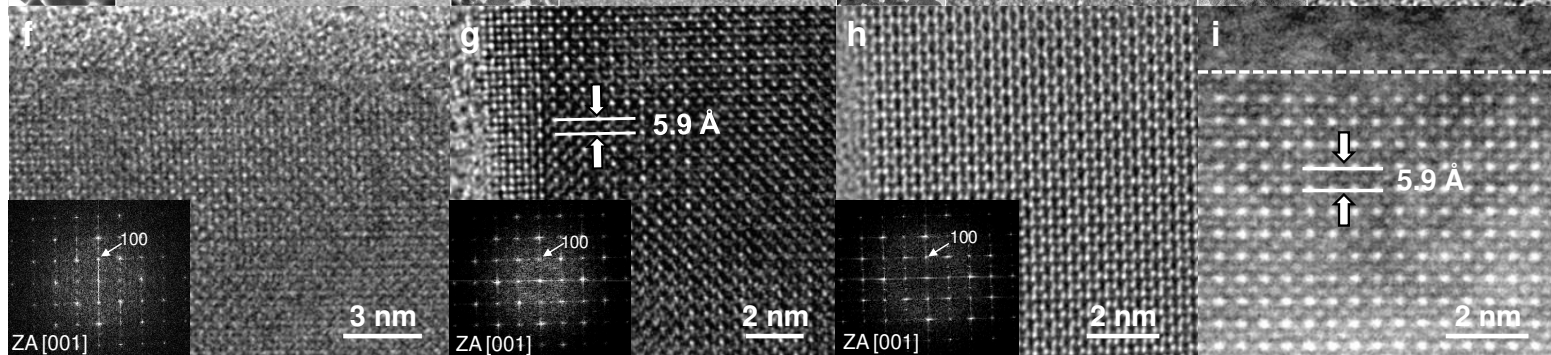
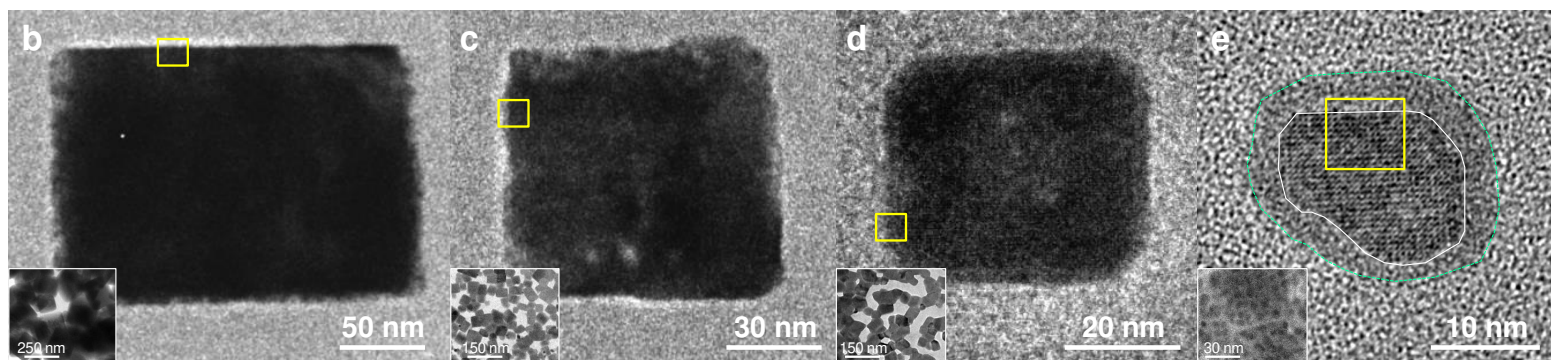
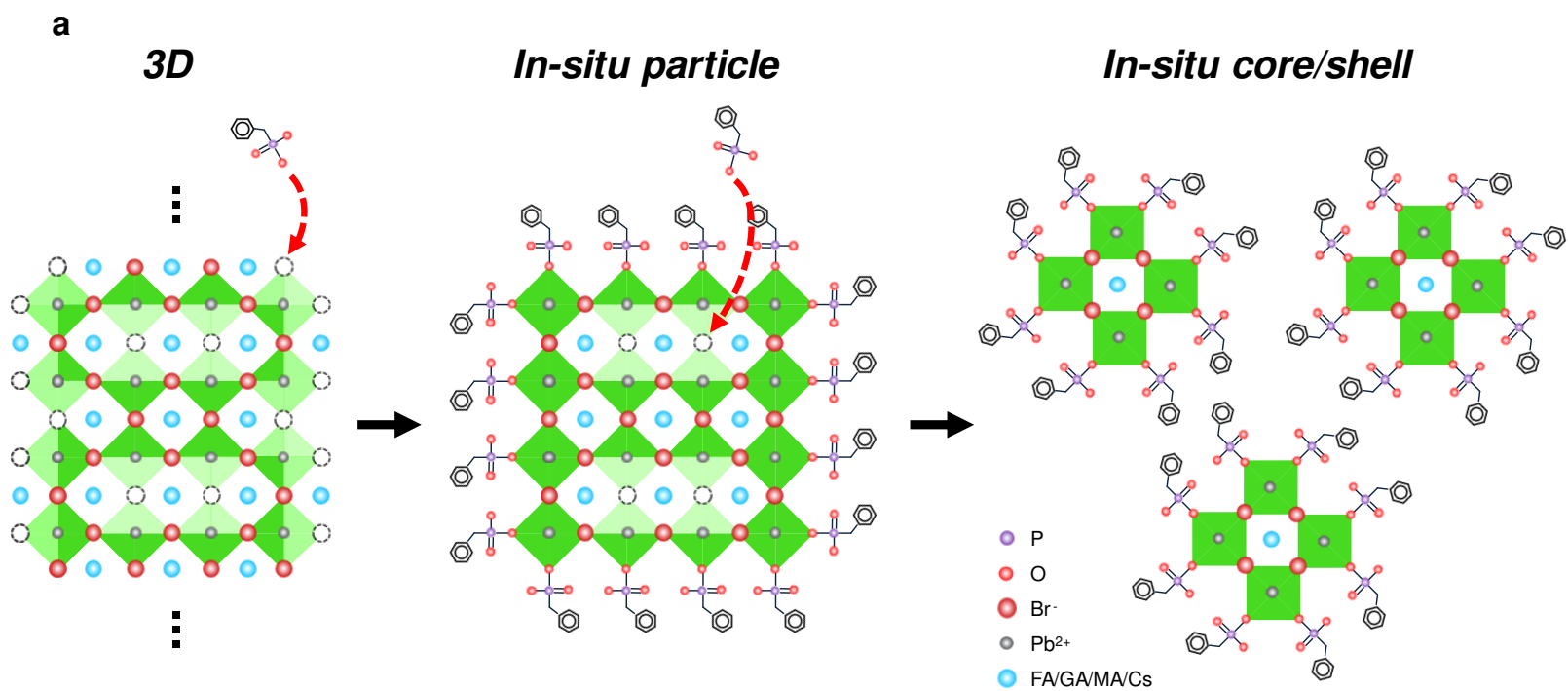
539 **Extended Data Fig. 6 | Photoluminescence characteristics of perovskite thin films.** **a**, PL
540 spectra and **b**, normalized PL spectra of quartz/perovskite thin film measured in integrating
541 sphere. **c**, External PLQE vs internal radiation efficiency (η_{rad}) (i.e. internal quantum efficiency,
542 IQE) of perovskite film calculated considering the influence of perovskite reabsorption^{30,31}.
543 The external PLQE of *in-situ* core/shell structure was 46 %, which corresponds to IQE of 88 %.
544 Temperature-dependent PL spectrum and corresponding integrated PL intensity with calculated
545 activation energy of **d,g**, 3D, **e,h**, *in-situ* particle, **f,i**, *in-situ* core-shell perovskite thin films.

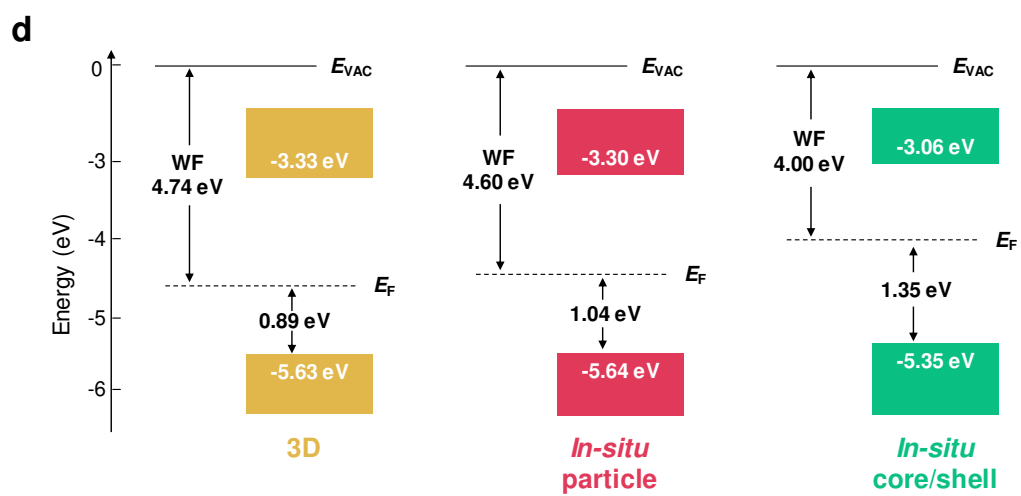
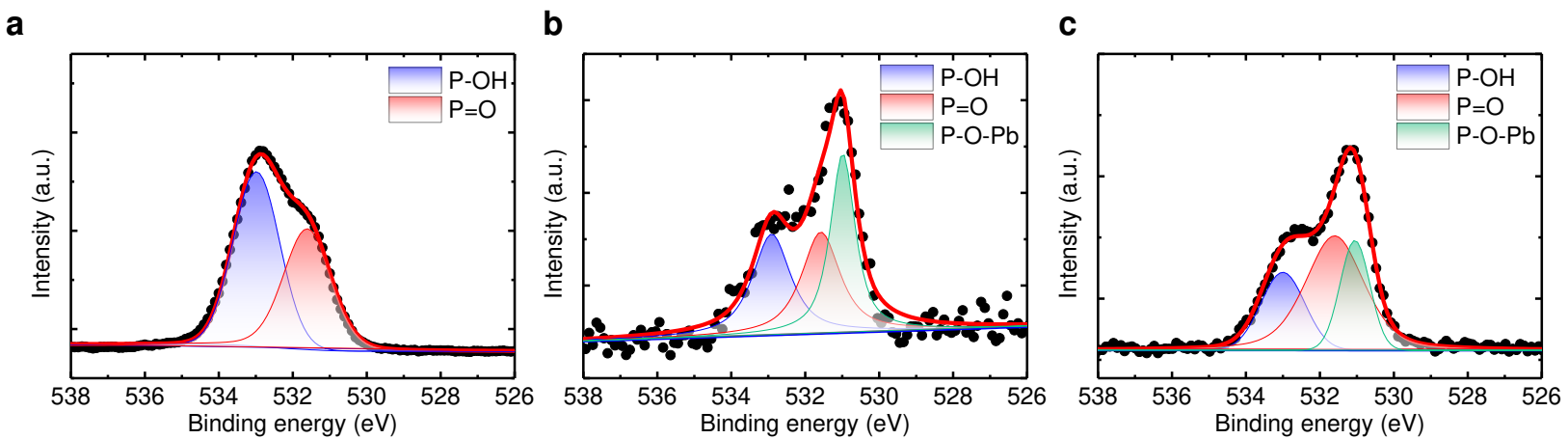
546 **Extended Data Fig. 7 | Current-voltage-luminance characteristics of PeLEDs.** **a**, Current
547 density vs voltage; **b**, luminance vs current density; **c**, Normalized EL spectra; **d**, CIE
548 coordinate of *in-situ* core/shell PeLEDs. **e**, power efficiency vs luminance; **f**, current
549 efficiency vs luminance of PeLEDs based on 3D, *in-situ* particle, *in-situ* core/shell structure.
550 **g**, Angle-dependent EL intensity and **h**, luminance histogram of PeLEDs based on *in-situ*
551 core/shell structure. **i**, EQE histogram of the PeLEDs based on *in-situ* core/shell structure
552 with different processing condition. As the temperature of the glove box increases or the A-
553 NCP process is delayed, the grain size of the spin-coated perovskite thin film increases,
554 which slows the penetration of the BPA solution into perovskite crystal and prevents full
555 conversion of them into the *in-situ* core/shell structure.

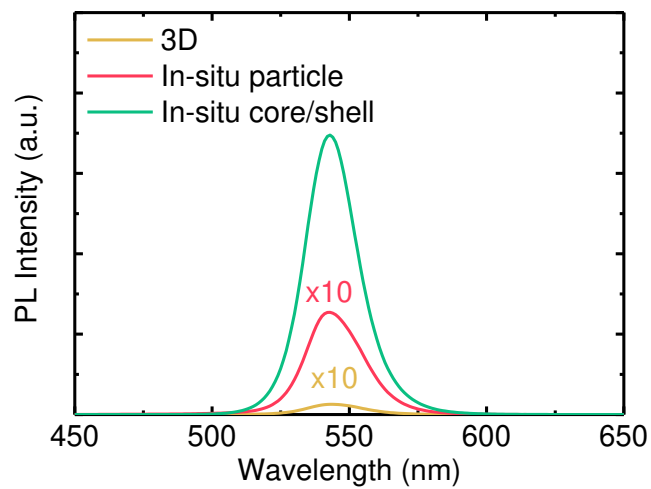
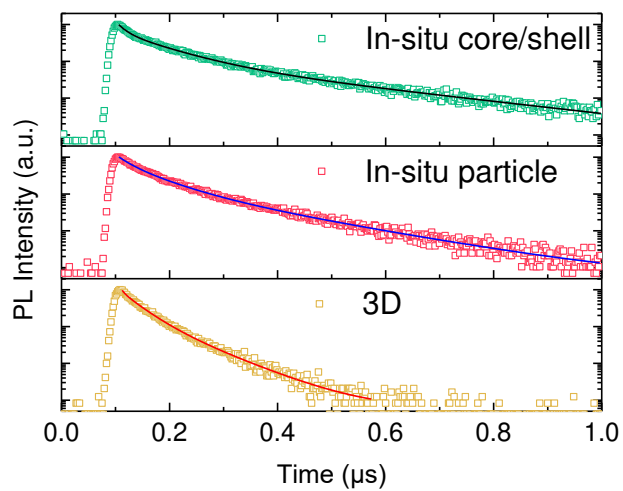
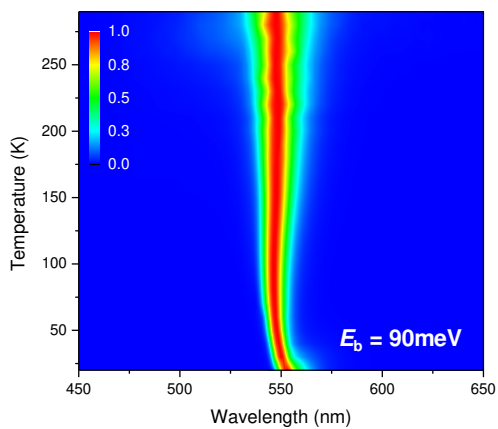
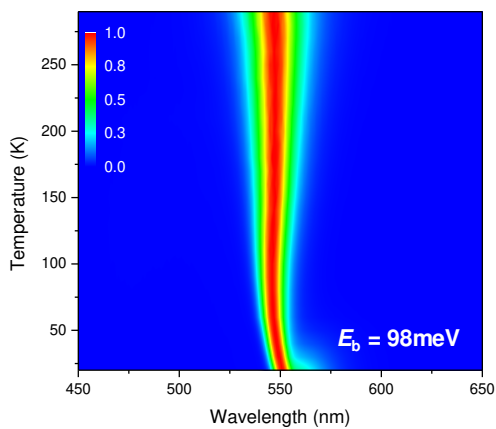
556 **Extended Data Fig. 8 | Large-area devices.** **a**, luminance vs voltage, **b**, EQE vs current
557 density of large-area devices based on *in-situ* core/shell perovskites. Photographs of large-area
558 devices (Pixel size: 120 mm²) operating at **c**, <10 cd m⁻², **d**, 1,000 cd m⁻², **e**, 100,000 cd m⁻²,
559 and **f**, 100,000 cd m⁻² under daylight, showing uniform emission over the pixel.

560 **Extended Data Fig. 9 | Operational lifetime of PeLEDs.** **a**, Luminance vs time of PeLEDs
561 based on 3D, *in-situ* particle, and *in-situ* core/shell perovskites at initial brightness of 10,000
562 cd m⁻² and **b**, corresponding driving voltage vs operation time.

563 **Extended Data Table 1 | Summarized electrical and luminance characteristics of PeLEDs.**
564 $V_{\text{turn-on}}$: Voltage at luminance of 1 cd m⁻², L_{max} : maximum luminance, EQE_{max} : maximum EQE,
565 CE_{max} : maximum current efficiency.





a**b****c****d****e**